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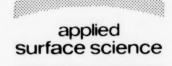
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Zirconium

Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in Pb(Ti_{0.48}Zr_{0.52})O₃ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo

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